Tables

 Table 1. Variables

Variable	Description	Initial value
V_{s}	transmembrane potential at the soma	-4.6 mV
V_D	transmembrane potential at the dendrite	-4.5 mV
h	K ⁺ channel activation gating variable	0.9990
n	Na^+ channel inactivation gating variable	0.001
S	Ca^{2+} channel activation gating variable	0.009
С	Ca^{2+} activated K^+ channel activation gating variable	0.007
q	K ⁺ AHP channel activation gating variable	0.010
c_{Ca}	Ca^{2+} concentration	0.200
S	NMDA synaptic conductance weighting factor	0.6
W	AMPA synaptic conductance weighting factor	0.5
	Currents: lower case (i) in current per unit membrane are	ea.
I_S, i_S	total transmembrane current at the soma	
$I_{\scriptscriptstyle D},i_{\scriptscriptstyle D}$	total transmembrane current at the dendrite	
$I_{S,leak}$, $i_{S,leak}$	transmembrane leakage current at the soma	
$I_{\scriptscriptstyle D,leak}$ $,i_{\scriptscriptstyle D,leak}$	transmembrane leakage current at the dendrite	
I_{Na} $,i_{Na}$	transmembrane Na^+ current	
I_{KDR} , i_{KDR}	transmembrane K ⁺ DR current	
$I_{\it KAHP}$ $,i_{\it KAHP}$	transmembrane K^+ AHP current	
I_{KC} $,i_{\mathit{KC}}$	transmembrane Ca^{2+} -activated K^+ current	
$I_{\it Ca},i_{\it Ca}$	transmembrane Ca^{2+} current	
I_{syn} , i_{syn}	total transmembrane synaptic current	
I_{DS}^{in}	intracelluar dendrite-to-soma current	
I_{DS}^{out}	extracellular dendrite-to-soma current	
V_S^{in}	intracellular potential at the soma	
$V_{\scriptscriptstyle D}^{\scriptscriptstyle in}$	intracellular potential at the dendrite	
V_{DS}^{out}	extracellular dendrite-soma potential difference	

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 Table 2. Parameters

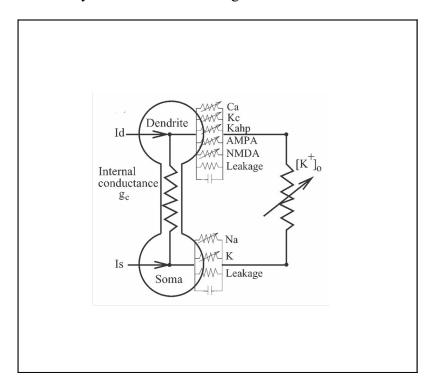
Parameter	Description	Value
A	total membrane area	$6 \times 10^{-6} \text{ cm}^2$
p	soma area/total membrane area	0.5 (unitless)
C_m	membrane capacitance	$2.1 \mu\text{F/cm}^2$
g_c	intracellular conductance	3.0 mS/cm ²
$g_{\scriptscriptstyle L}$	leakage conductance	0.1 mS/cm ²
g_{Na}	Na^+ channel conductance	30.0 mS/cm ²
$g_{\scriptscriptstyle KDR}$	K^+ (delayed-rectifier) channel conductance	15.0 mS/cm ²
$g_{\it KAHP}$	K ⁺ AHP conductance	0.80 mS/cm^2
$g_{\scriptscriptstyle KC}$	Ca^{2+} -activated K^+ channel conductance	15.0 mS/cm^2
$g_{\it Ca}$	Ca^{2+} channel conductance	10.0 mS/cm^2
g_{NMDA}	NMDA channel synaptic conductance	$0.030~\mathrm{mS/cm^2}$
g_{AMPA}	AMPA channel synaptic conductance	0.0045 mS/cm ²
V_{app}	externally applied potential	0 to -50 <i>mV</i>
I_S^{inj}	injected current at the soma	0 mV
$I_D^{\it inj}$	injected current at the dendrite	
Reversal poter	tials with respect to reference potential of -60 mV	
V_{Na}		120 mV
V_{Ca}		140 mV
V_{K}	$[K^+]_0 = 3.5 \ mM$	-38.56 mV
V_L		0~mV
V_{syn}		60 mV
Extracellular r	esistances	
R_{TD}^{out}	extracellular resistance between the top plate and the dendrite	
R_{SG}^{out}	extracellular resistance between the soma and ground	
R_{DS}^{out}	extracellular resistance between the dendrite and the soma	7936.5 $k\Omega$

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R	$R_{TD} = R_{SG} = R$	$12 \times R_{DS}^{out}$
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Figure 1.

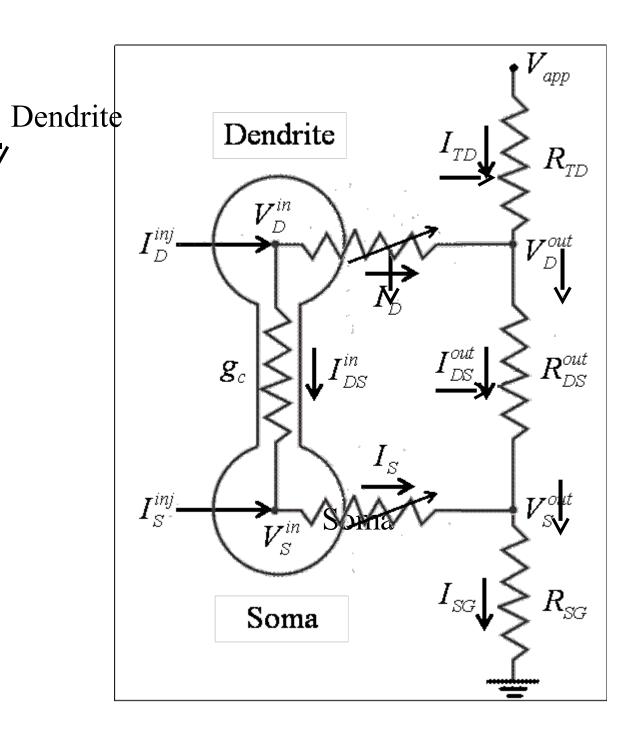
A. Pinsky-Rinzel model of a single neuron.



Re-do to match Figure 1B. Also remove [K].

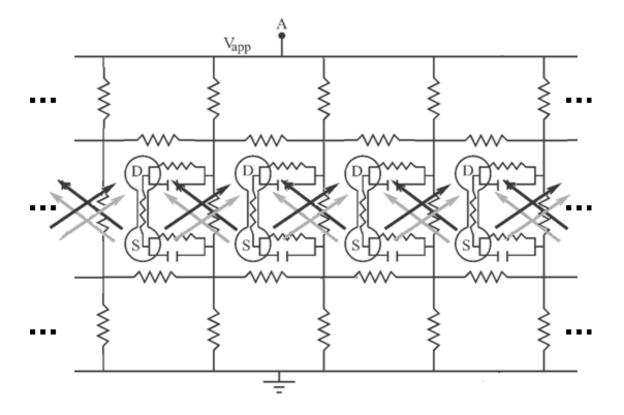
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B. A single Pinsky-Rinzel neuron under the effect of an externally applied field.



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Figure 2. Model of Pinsky-Rinzel arranged in a one-dimensional chain and embedded in an extracellular resistive grid. Each neuron is connected synaptically with its nearest-neighbors.



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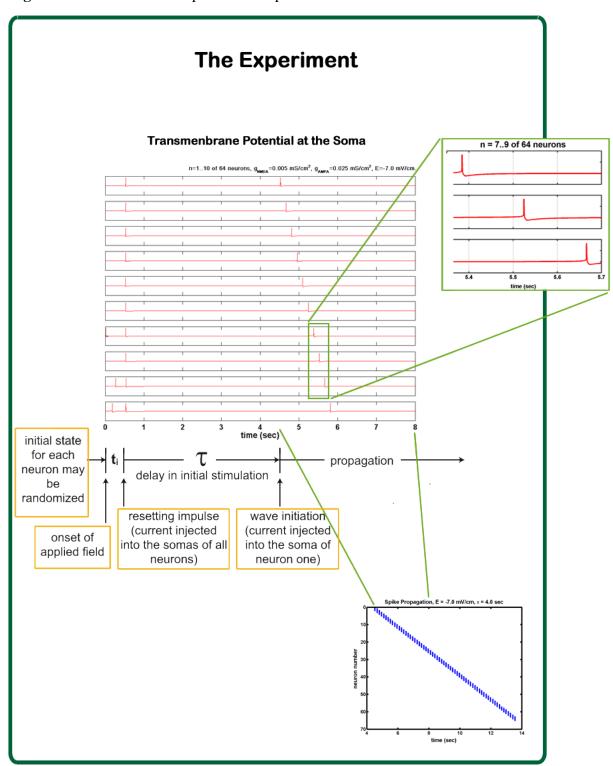


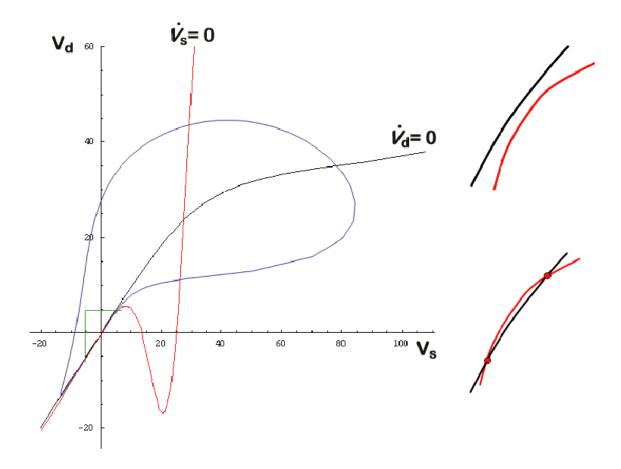
Figure 3. Timeline of a computational experiment.

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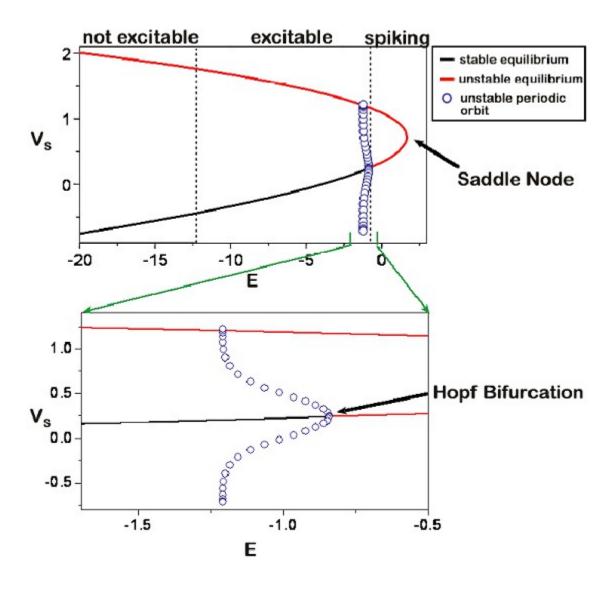
Re-do as a full page figure.

Figure 4. Dynamics of the single neuron model.

Redo with grey scale.



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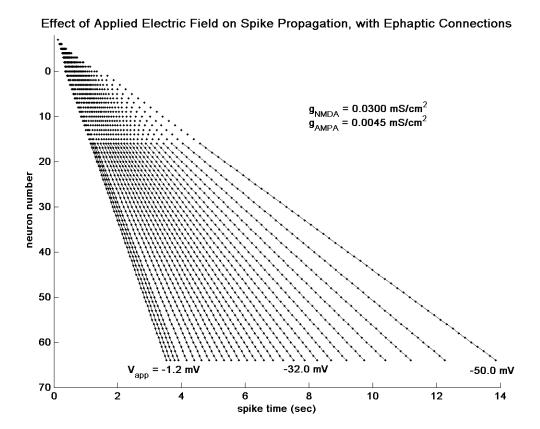
(No Figure 5)

Figure 6. Example of traces of membrane potential at the soma at various applied potentials. **A)** At low applied potential where spiking activity was observed. **B)** At medium suppressive applied potential strength where propagation was observed. **c)** At high applied potential where propagation was completely terminated.

Wait for final data.

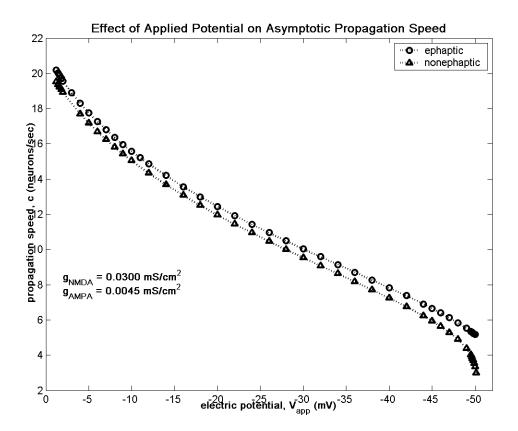
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Figure 7. The effect of an applied electric field on propagation speed.



A.

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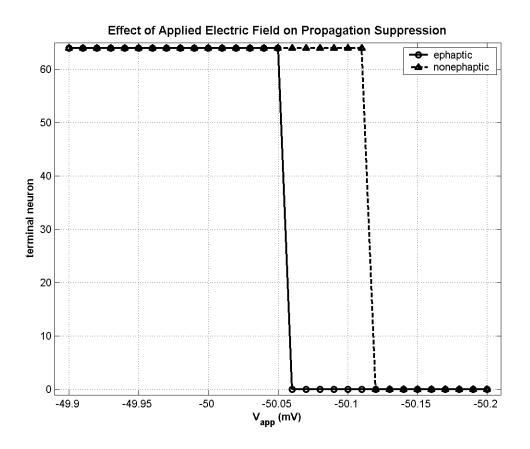


Need to edit and point out V_1^* and V_2^* .

B.

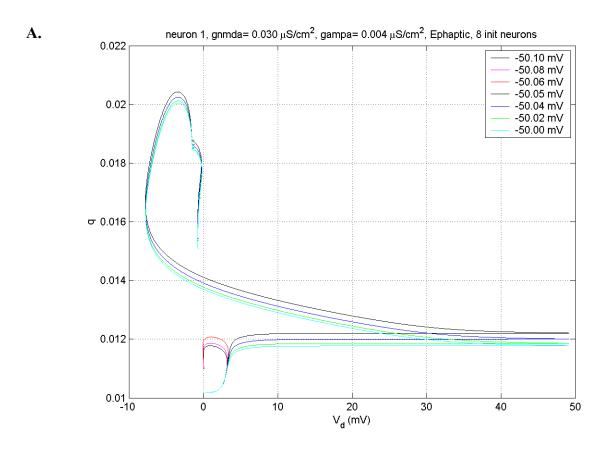
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Figure 8. The effect an applied electric field on spike wave propagation near the point of suppression, with and without ephaptic connection among neurons.



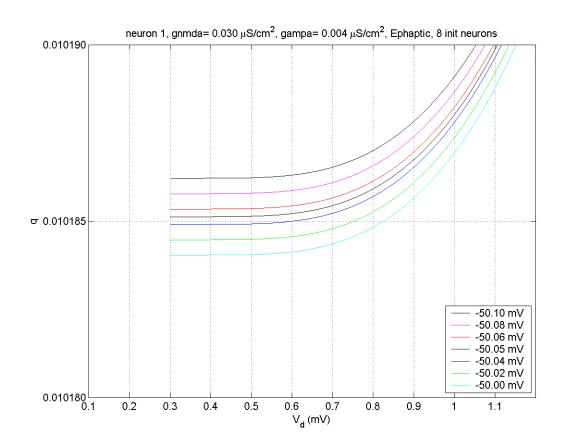
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Figure 9. Phase-plane analysis of spike-wave propagation near suppression



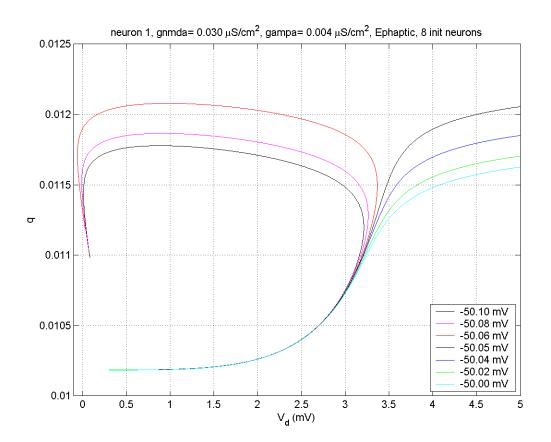
This diagram shows the trajectories of the q-V as a function of applied potential V_{top} . Spike-propagation occurs when V_{top} is -50.05 mV or less negative. Spike-progation is suppressed when V_{top} is -50.06 or more negative. Several areas of the diagram are expanded in details.

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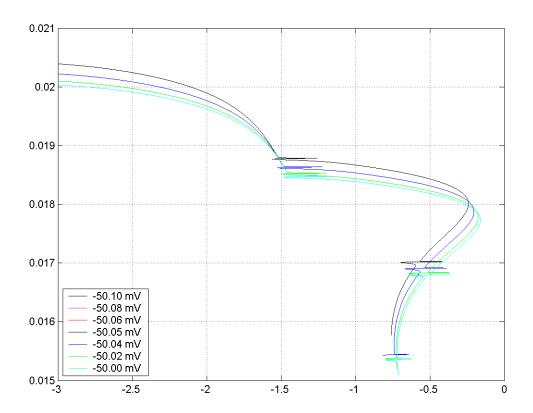
B. At equilibrium, the trajectories are ranked in order according to the applied potentialV_app.

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C. At the

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D. Trajectories for propagation are expanded at the region when neuronal activity is retuning to equilibrium. This figure displays the effects of backward synaptic connection and ephaptic interaction.

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